

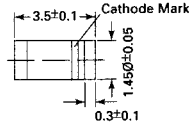
LL101A ... LL101C

Silicon Schottky Barrier Diode for general purpose applications

The LL101 Series is a metal on silicon Schottky barrier device which is protected by a PN junction guard ring. The low forward voltage drop and fast switching make it ideal for protection of MOS devices, steering, biasing and coupling diodes for fast switching and low logic level applications.

This diode is also available in DO-35 case with type designation SD101A, B, C.

These diodes are delivered taped.
Details see "Taping".



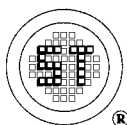
Glass case MiniMELF

Weight approx. 0.05g
Dimensions in mm

Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

	Symbol	Value	Unit
Peak Reverse Voltage	LL101A V_{RRM}	60	V
	LL101B V_{RRM}	50	V
	LL101C V_{RRM}	40	V
Power Dissipation (Infinite Heatsink)	P_{tot}	400 ¹⁾	mW
Max. Single Cycle Surge 10 μ s Squarewave	I_{FSM}	2	A
Junction Temperature	T_j	200	$^\circ\text{C}$
Storage Temperature Range	T_s	-55 to + 200	$^\circ\text{C}$

¹⁾ Valid provided that electrodes are kept at ambient temperature.



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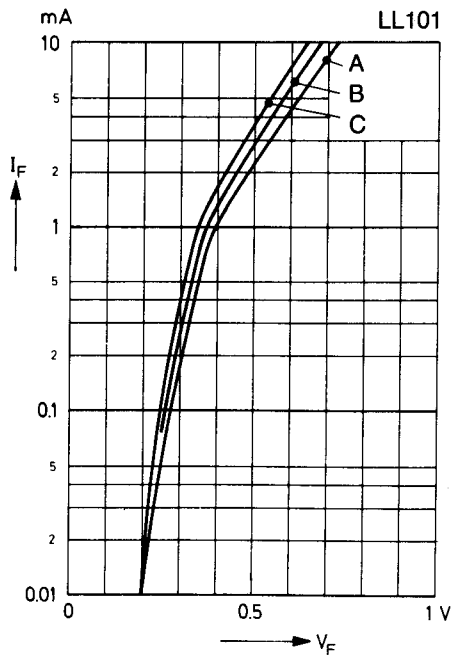


LL101A ... LL101C

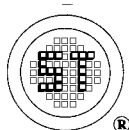
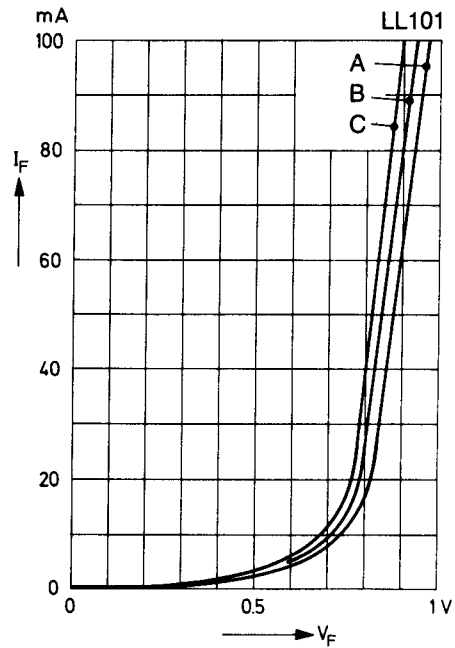
Characteristics at $T_{amb} = 25\text{ }^{\circ}\text{C}$

		Symbol	Min.	Typ.	Max.	Unit
Reverse Breakdown Voltage at $I_R = 10\text{ }\mu\text{A}$	LL101A	$V_{(BR)R}$	60	-	-	V
	LL101B	$V_{(BR)R}$	50	-	-	V
	LL101C	$V_{(BR)R}$	40	-	-	V
Leakage Current at $V_R = 50\text{ V}$ at $V_R = 40\text{ V}$ at $V_R = 30\text{ V}$	LL101A	I_R	-	-	200	nA
	LL101B	I_R	-	-	200	nA
	LL101C	I_R	-	-	200	nA
Forward Voltage Drop at $I_F = 1\text{ mA}$ at $I_F = 15\text{ mA}$	LL101A	V_F	-	-	0.41	V
	LL101B	V_F	-	-	0.4	V
	LL101C	V_F	-	-	0.39	V
	LL101A	V_F	-	-	1	V
	LL101B	V_F	-	-	0.95	V
	LL101C	V_F	-	-	0.9	V
Junction Capacitance at $V_R = 0\text{ V}$, $f = 1\text{ MHz}$	LL101A	C_{tot}	-	-	2.0	pF
	LL101B	C_{tot}	-	-	2.1	pF
	LL101C	C_{tot}	-	-	2.2	pF
Reverse Recovery Time at $I_F = I_R = 5\text{ mA}$, recover to $0.1\text{ }I_R$		t_{rr}	-	-	1	ns

Typical variation of fwd. current vs. fwd. voltage for primary conduction through the Schottky barrier



Typical forward conduction curve of combination Schottky barrier and PN junction guard ring

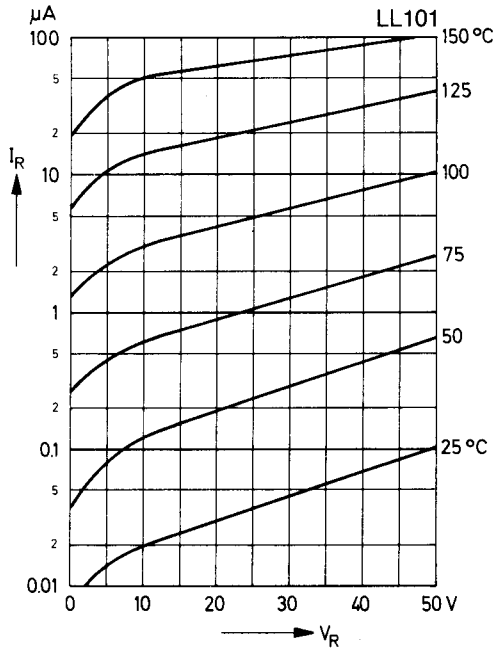


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Typical variation of reverse current at various temperatures



Typical capacitance curve as a function of reverse voltage

